



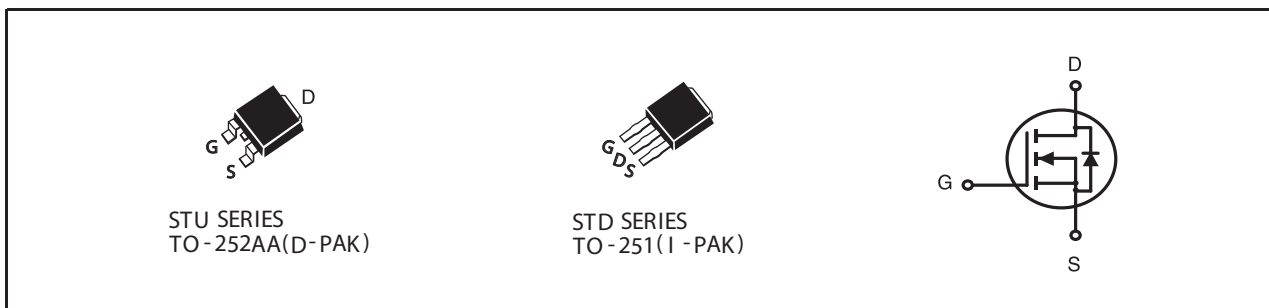
## N-Channel Logic Level Enhancement Mode Field Effect Transistor

### PRODUCT SUMMARY

VDSS	ID	RDS(ON) (mΩ) Max
100V	5A	620 @ VGS=10V
		721 @ VGS=4.5V

### FEATURES

- Super high dense cell design for low RDS(ON).
- Rugged and reliable.
- TO-252 and TO-251 Package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V <sub>DS</sub>	Drain-Source Voltage	100	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous <sup>c</sup>	T <sub>C</sub> =25°C	5
		T <sub>C</sub> =70°C	4
I <sub>DM</sub>	-Pulsed <sup>a,c</sup>	14	A
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>d</sup>	4	mJ
P <sub>D</sub>	Maximum Power Dissipation	T <sub>C</sub> =25°C	42
		T <sub>C</sub> =70°C	27
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C

### THERMAL CHARACTERISTICS

Symbol	Parameter	Limit	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	50	°C/W

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### ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =10mA	100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =80V , V <sub>GS</sub> =0V			1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTICS</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.8	3	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V , I <sub>D</sub> =2.5A		496	620	m ohm
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =2.3A		534	721	m ohm
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =10V , I <sub>D</sub> =2.5A		8		S
<b>DYNAMIC CHARACTERISTICS<sup>b</sup></b>						
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V f=1.0MHz		245		pF
C <sub>OSS</sub>	Output Capacitance			22		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			14		pF
<b>SWITCHING CHARACTERISTICS<sup>b</sup></b>						
t <sub>D(ON)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V I <sub>D</sub> =1A		8		ns
t <sub>r</sub>	Rise Time			10		ns
t <sub>D(OFF)</sub>	Turn-Off Delay Time	V <sub>GS</sub> =10V R <sub>GEN</sub> = 6 ohm		15.5		ns
t <sub>f</sub>	Fall Time			2.6		ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =50V, I <sub>D</sub> =2.5A, V <sub>GS</sub> =10V		4.3		nC
		V <sub>DS</sub> =50V, I <sub>D</sub> =2.5A, V <sub>GS</sub> =4.5V		2.3		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =50V, I <sub>D</sub> =2.5A, V <sub>GS</sub> =10V		0.8		nC
Q <sub>gd</sub>	Gate-Drain Charge			1.4		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A		0.82	1.3	V

#### Notes

- Pulse Test: Pulse Width ≤ 10μs, Duty Cycle ≤ 1%.
- Guaranteed by design, not subject to production testing.
- Drain current limited by maximum junction temperature.
- Starting T<sub>J</sub>=25°C, L=0.5mH, V<sub>DD</sub> = 50V. (See Figure13)
- Mounted on FR4 Board of 1 inch<sup>2</sup> , 2oz.

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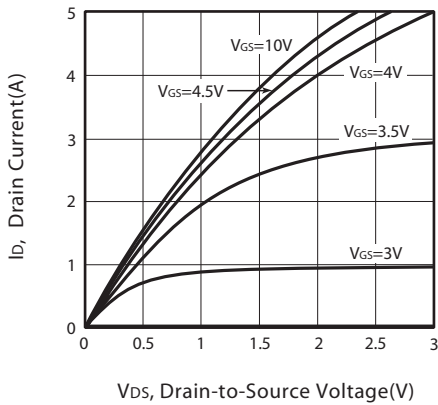


Figure 1. Output Characteristics

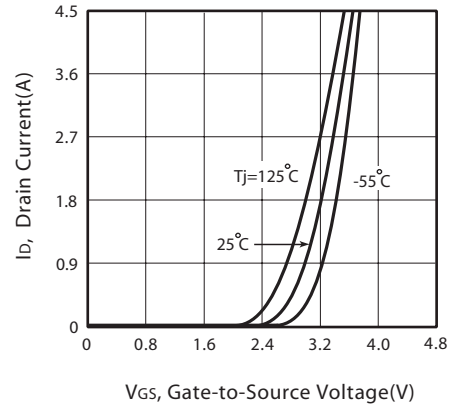


Figure 2. Transfer Characteristics

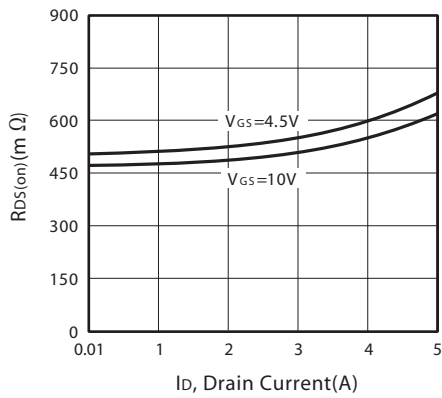


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

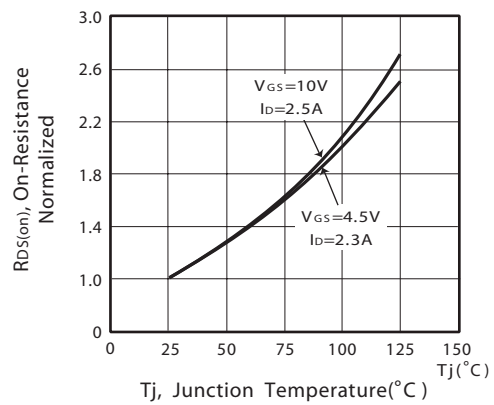


Figure 4. On-Resistance Variation with Drain Current and Temperature

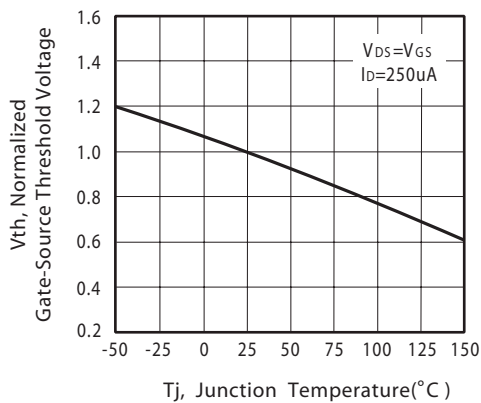


Figure 5. Gate Threshold Variation with Temperature

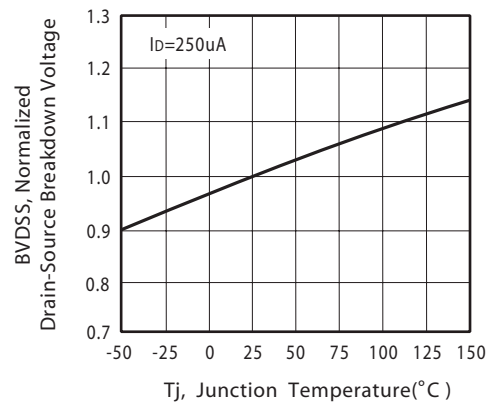


Figure 6. Breakdown Voltage Variation with Temperature

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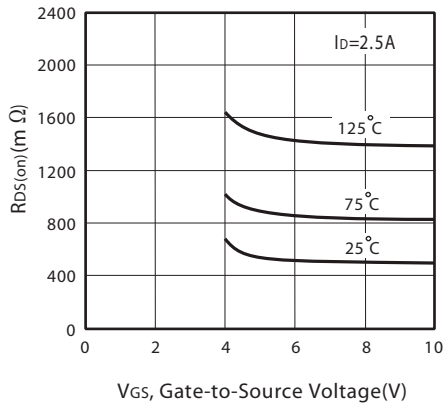


Figure 7. On-Resistance vs. Gate-Source Voltage

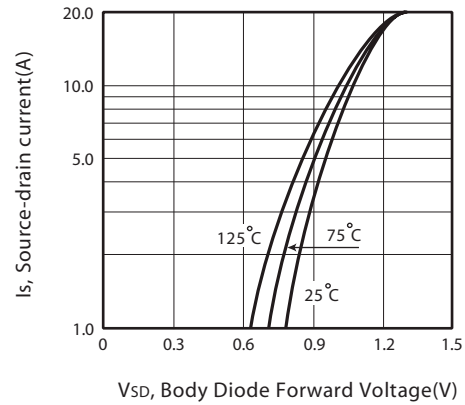


Figure 8. Body Diode Forward Voltage Variation with Source Current

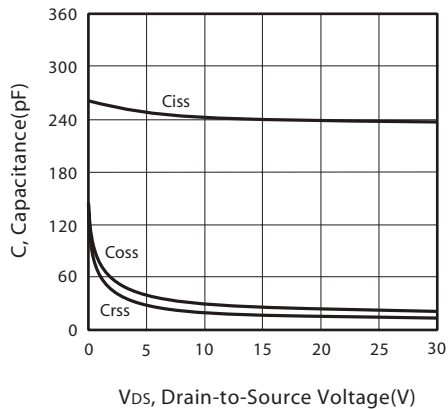


Figure 9. Capacitance

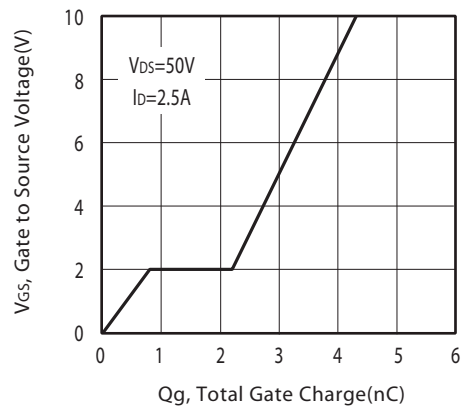


Figure 10. Gate Charge

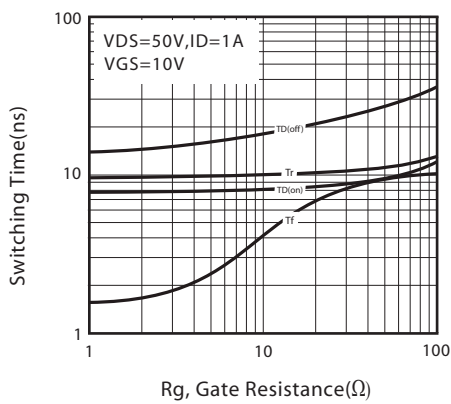


Figure 11. switching characteristics

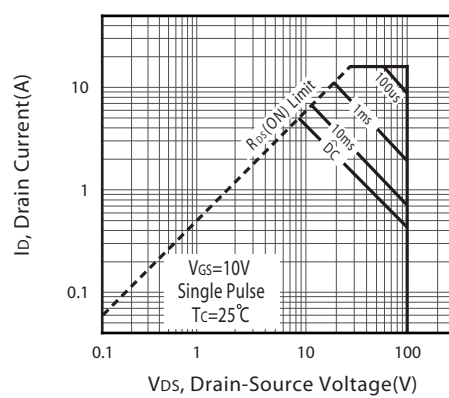
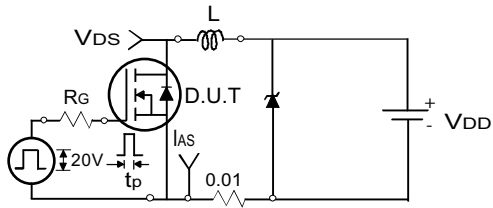


Figure 12. Maximum Safe Operating Area

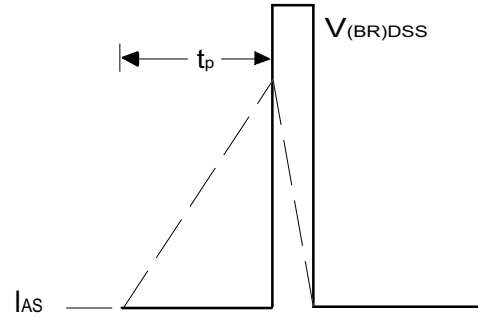
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Uncamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

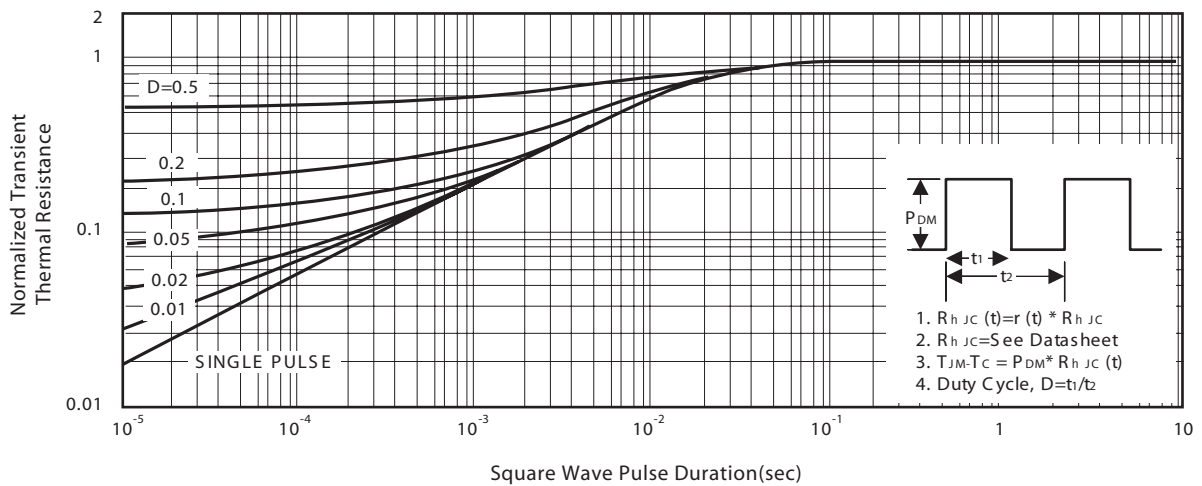
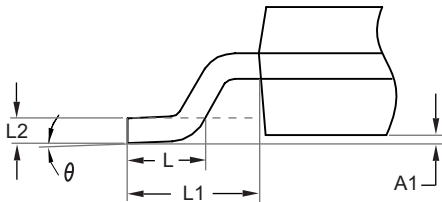
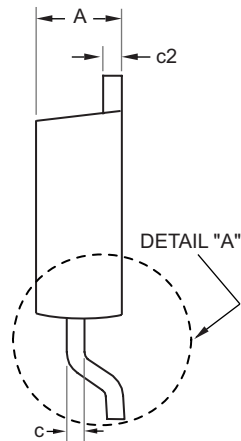
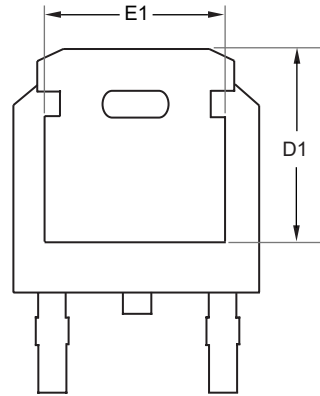
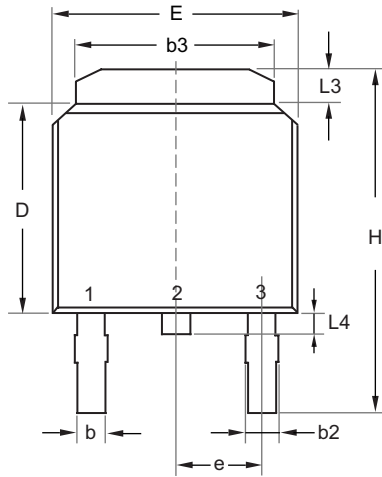


Figure 14. Normalized Thermal Transient Impedance Curve

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## TO-252



DETAIL "A"

SYMBOLS	MILLIMETERS	
	MIN	MAX
A	2.200	2.380
A1	0.000	0.127
b	0.635	0.889
b2	0.762	1.143
b3	5.200	5.460
c	0.450	0.600
c2	0.450	0.580
D	6.000	6.223
D1	5.210	5.380
e	2.286 BSC	
E	6.400	6.731
E1	4.318	4.900
H	9.400	10.400
L	1.400	1.770
L1	2.743 REF	
L2	0.508 BSC	
L3	0.890	1.270
L4	0.640	1.010
$\theta$	0°	10°

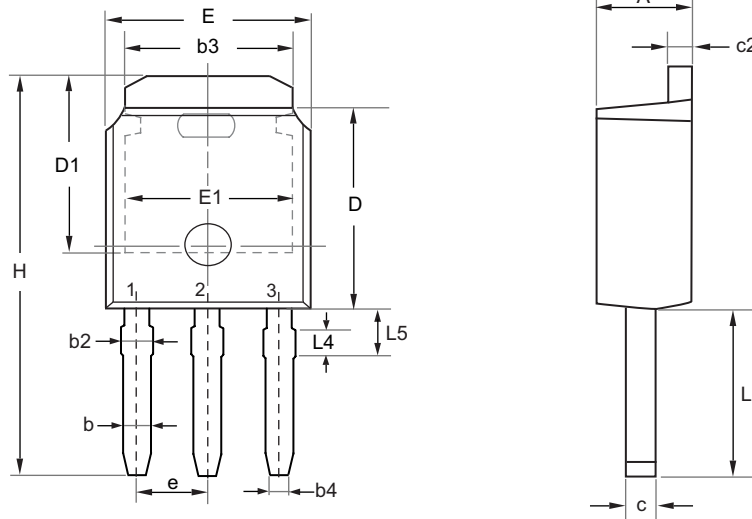
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## PACKAGE OUTLINE DIMENSIONS

TO-251



SYMBOL	MILLIMETERS	
	MIN	MAX
E	6.350	6.731
L	3.700	4.400
L4	0.698 REF	
L5	0.972	1.226
D	5.970	6.223
H	9.670	11.450
b	0.630	0.850
b2	0.760	1.140
b3	4.950	5.460
b4	0.450	0.550
e	2.286 BSC	
A	2.180	2.390
c	0.400	0.610
c2	0.400	0.610
D1	5.100	---
E1	4.318	---

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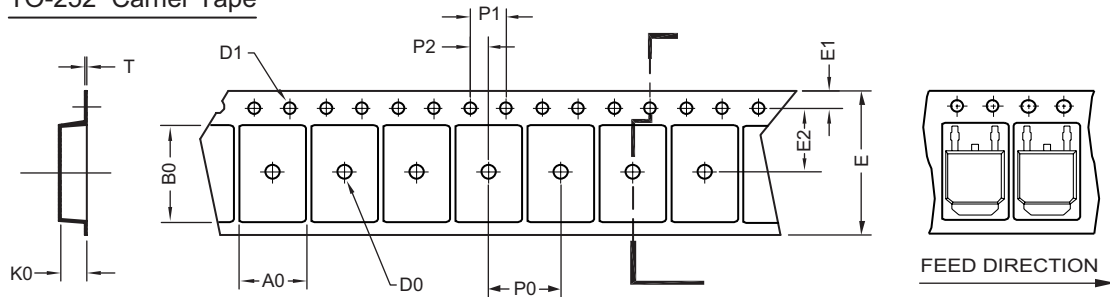
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## TO-251 Tube/TO-252 Tape and Reel Data

### TO-251 Tube



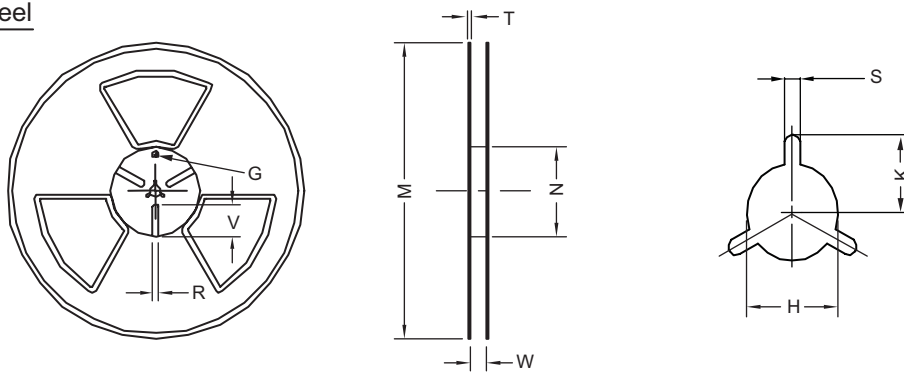
### TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

### TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---

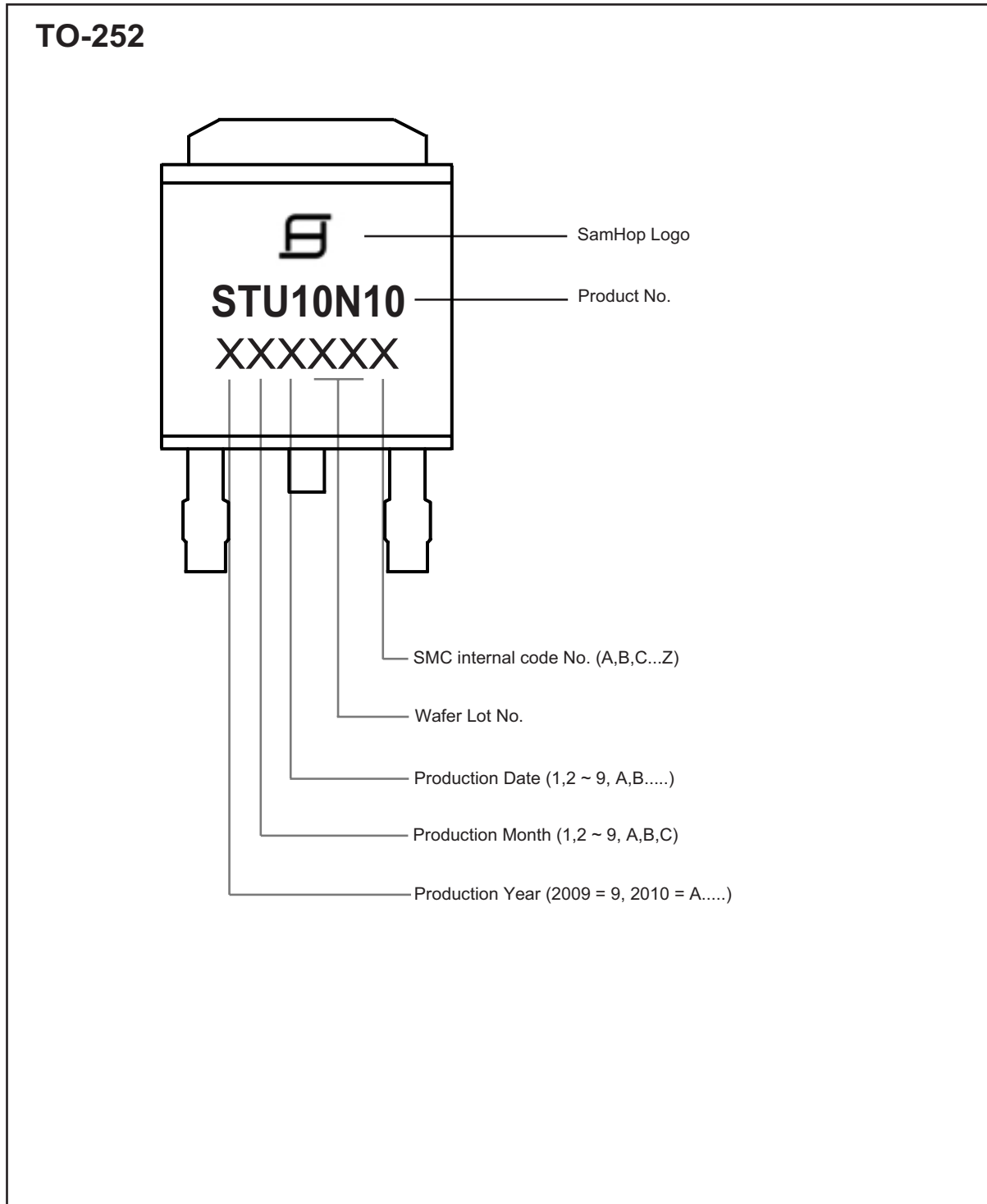
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## TOP MARKING DEFINITION

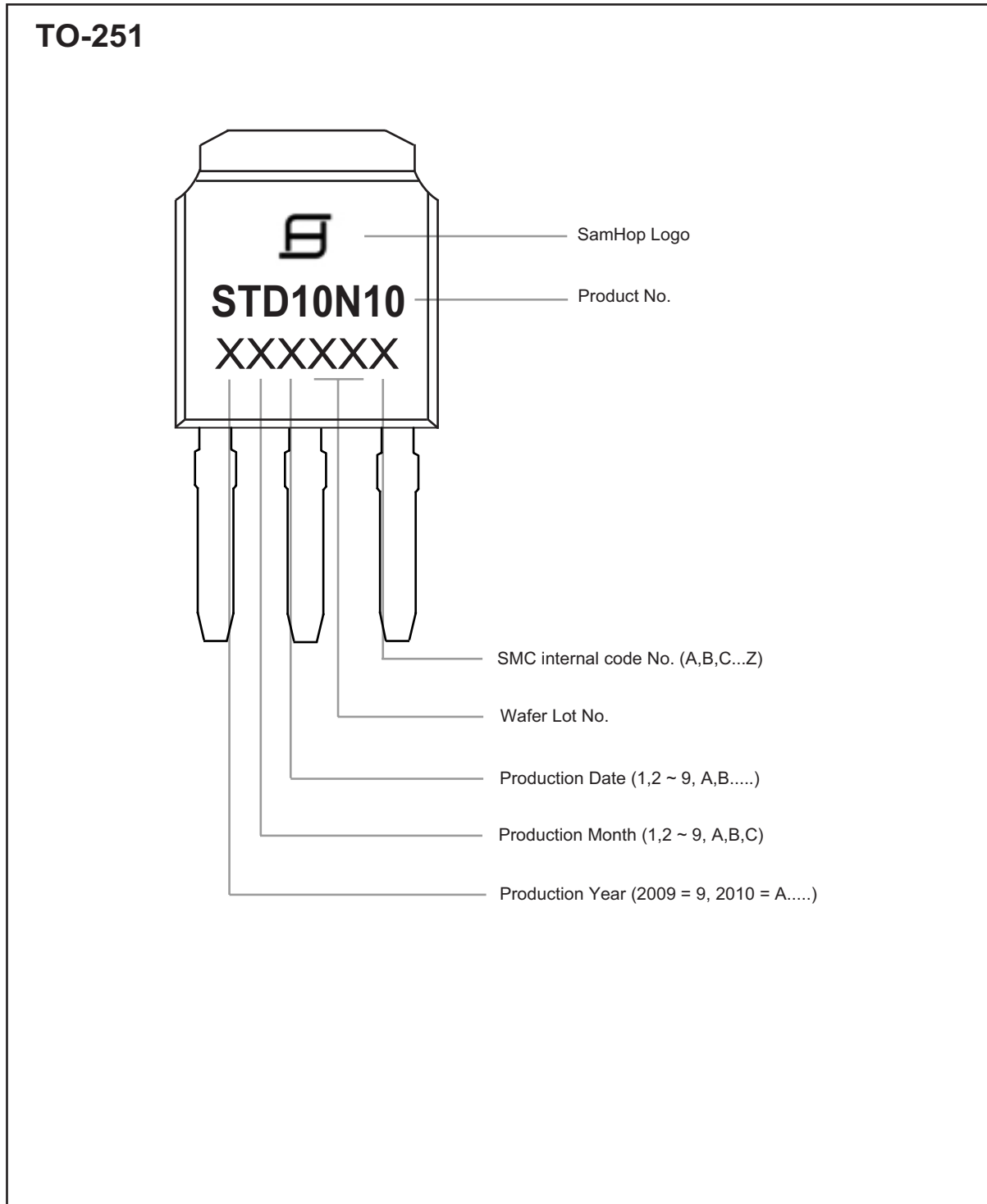


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## TOP MARKING DEFINITION



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